

CoolMOS™ Power Transistor
Features

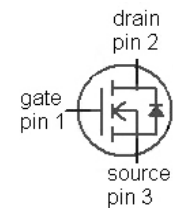
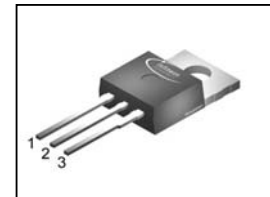
- Intrinsic fast-recovery body diode
- Extremely low reverse recovery charge
- Ultra low gate charge
- Extreme dv/dt rated
- High peak current capability
- Qualified according to JEDEC¹⁾ for target applications

CoolMOS CFD designed for:

- Soft switching PWM Stages
- LCD & CRT TV

Product Summary

| | | |
|---------------------|-----|----------|
| $V_{DS} @ T_{jmax}$ | 650 | V |
| $R_{DS(on),max}$ | 0.7 | Ω |
| I_D | 6.6 | A |

PG-TO220


| Type | Package | Marking |
|-------------|----------|----------|
| SPP07N60CFD | PG-TO220 | 07N60CFD |

Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Value | Unit |
|--|-------------------|---|-------------|--------------------|
| Continuous drain current | I_D | $T_C=25\text{ °C}$ | 6.6 | A |
| | | $T_C=100\text{ °C}$ | 4.3 | |
| Pulsed drain current ²⁾ | $I_{D,pulse}$ | $T_C=25\text{ °C}$ | 17 | |
| Avalanche energy, single pulse | E_{AS} | $I_D=3.3\text{ A}$, $V_{DD}=50\text{ V}$ | 230 | mJ |
| Avalanche energy, repetitive ^{2),3)} | E_{AR} | $I_D=6.6\text{ A}$, $V_{DD}=50\text{ V}$ | 0.5 | |
| Avalanche current, repetitive ^{2),3)} | I_{AR} | | 6.6 | A |
| Drain source voltage slope | dv/dt | $I_D=6.6\text{ A}$, $V_{DS}=480\text{ V}$, $T_j=125\text{ °C}$ | 80 | V/ns |
| Reverse diode dv/dt | dv/dt | $I_S=6.6\text{ A}$, $V_{DS}=480\text{ V}$, $T_j=125\text{ °C}$ | 40 | V/ns |
| Maximum diode commutation speed | di/dt | $T_j=125\text{ °C}$ | 600 | A/ μ s |
| Gate source voltage | V_{GS} | static | ± 20 | V |
| | | AC ($f>1\text{ Hz}$) | ± 30 | |
| Power dissipation | P_{tot} | $T_C=25\text{ °C}$ | 83 | W |
| Operating and storage temperature | T_j , T_{stg} | | -55 ... 150 | $^{\circ}\text{C}$ |
| Mounting torque | | M3 & M3.5 screws | 60 | Ncm |

| Parameter | Symbol | Conditions | Values | | | Unit |
|-----------|--------|------------|--------|------|------|------|
| | | | min. | typ. | max. | |

Thermal characteristics

| | | | | | | |
|---|------------|---------------------------------------|---|---|-----|-----|
| Thermal resistance, junction - case | R_{thJC} | | - | - | 1.5 | K/W |
| Thermal resistance, junction - ambient | R_{thJA} | leaded | - | - | 62 | |
| Soldering temperature, wave soldering only allowed at leads | T_{sold} | 1.6 mm (0.063 in.) from case for 10 s | - | - | 260 | °C |

Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified

Static characteristics

| | | | | | | |
|----------------------------------|---------------|---|-----|------|-----|---------------|
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | $V_{GS}=0\text{ V}$, $I_D=250\text{ }\mu\text{A}$ | 600 | - | - | V |
| Avalanche breakdown voltage | $V_{(BR)DS}$ | $V_{GS}=0\text{ V}$, $I_D=6.6\text{ A}$ | - | 700 | - | |
| Gate threshold voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}$, $I_D=300\text{ }\mu\text{A}$ | 3 | 4 | 5 | |
| Zero gate voltage drain current | I_{DSS} | $V_{DS}=600\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$ | - | 0.6 | - | μA |
| | | $V_{DS}=600\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=150\text{ °C}$ | - | 630 | - | |
| Gate-source leakage current | I_{GSS} | $V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$ | - | - | 100 | nA |
| Drain-source on-state resistance | $R_{DS(on)}$ | $V_{GS}=10\text{ V}$, $I_D=4.6\text{ A}$, $T_j=25\text{ °C}$ | - | 0.59 | 0.7 | Ω |
| | | $V_{GS}=10\text{ V}$, $I_D=4.6\text{ A}$, $T_j=150\text{ °C}$ | - | 1.6 | - | |
| Gate resistance | R_G | $f=1\text{ MHz}$, open drain | - | 1.2 | - | |
| Transconductance | g_{fs} | $ V_{DS} >2 I_D R_{DS(on)max}$, $I_D=4.6\text{ A}$ | - | 5.0 | - | S |

| Parameter | Symbol | Conditions | Values | | | Unit |
|-----------|--------|------------|--------|------|------|------|
| | | | min. | typ. | max. | |

Dynamic characteristics

| | | | | | | |
|--|--------------|--|---|-----|---|----|
| Input capacitance | C_{iss} | $V_{GS}=0\text{ V}, V_{DS}=25\text{ V},$ $f=1\text{ MHz}$ | - | 790 | - | pF |
| Output capacitance | C_{oss} | | - | 260 | - | |
| Reverse transfer capacitance | C_{rss} | | - | 16 | - | |
| Effective output capacitance, energy related ⁴⁾ | $C_{o(er)}$ | $V_{GS}=0\text{ V}, V_{DS}=0\text{ V}$ to 480 V | - | 30 | - | |
| Effective output capacitance, time related ⁵⁾ | $C_{o(tr)}$ | | - | 55 | - | |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD}=400\text{ V},$ $V_{GS}=10\text{ V}, I_D=6.6\text{ A},$ $R_G=6.8\ \Omega$ | - | 12 | - | ns |
| Rise time | t_r | | - | 25 | - | |
| Turn-off delay time | $t_{d(off)}$ | | - | 36 | - | |
| Fall time | t_f | | - | 9 | - | |

Gate Charge Characteristics

| | | | | | | |
|-----------------------|---------------|--|---|-----|----|----|
| Gate to source charge | Q_{gs} | $V_{DD}=480\text{ V}, I_D=6.6\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$ | - | 6.6 | - | nC |
| Gate to drain charge | Q_{gd} | | - | 20 | - | |
| Gate charge total | Q_g | | - | 35 | 47 | |
| Gate plateau voltage | $V_{plateau}$ | | - | 7.2 | - | V |

¹⁾ J-STD20 and JESD22

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ Repetitive avalanche causes additional power losses that can be calculated as $P_{AV}=E_{AR} \cdot f$.

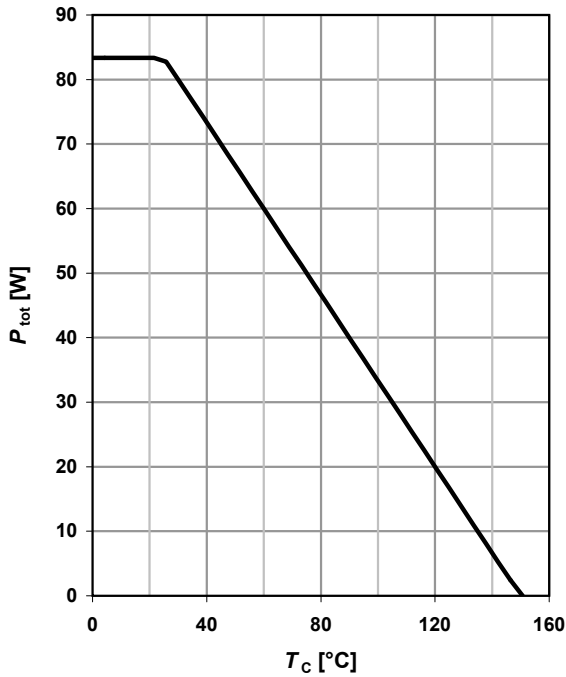
⁴⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

⁵⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

| Parameter | Symbol | Conditions | Values | | | Unit |
|---|---------------|--|--------|------|------|------------------------|
| | | | min. | typ. | max. | |
| Reverse Diode | | | | | | |
| Diode continuous forward current | I_S | $T_C=25\text{ °C}$ | - | - | 6.6 | A |
| Diode pulse current ²⁾ | $I_{S,pulse}$ | | - | - | 17 | |
| Diode forward voltage | V_{SD} | $V_{GS}=0\text{ V}, I_F=I_S,$ $T_j=25\text{ °C}$ | - | 1.0 | 1.2 | V |
| Reverse recovery time | t_{rr} | $V_R=480\text{ V}, I_F=I_S,$ $di_F/dt=100\text{ A}/\mu\text{s}$ | - | 104 | - | ns |
| Reverse recovery charge | Q_{rr} | | - | 0.5 | - | μC |
| Peak reverse recovery current | I_{rrm} | | - | 8 | - | A |
| Peak rate of fall of reverse recovery current | di_{rr}/dt | $T_j=25\text{ °C}$ | - | 1000 | - | $\text{A}/\mu\text{s}$ |

1 Power dissipation

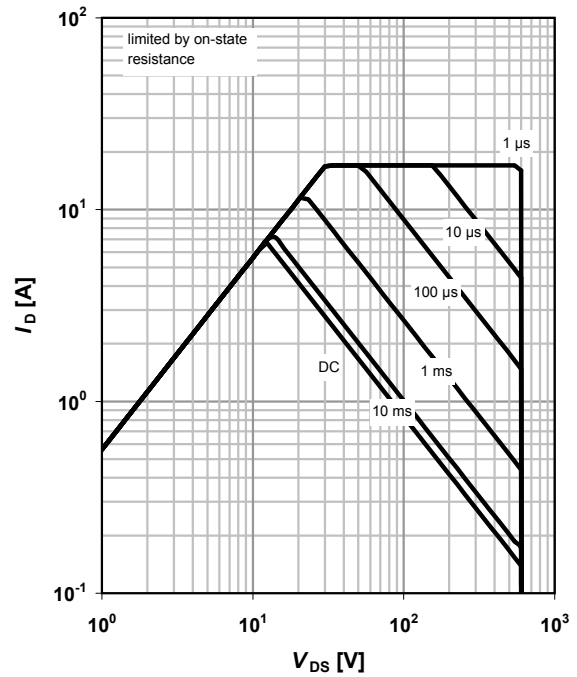
$P_{tot}=f(T_C)$



2 Safe operating area

$I_D=f(V_{DS}); T_C=25\text{ °C}; D=0$

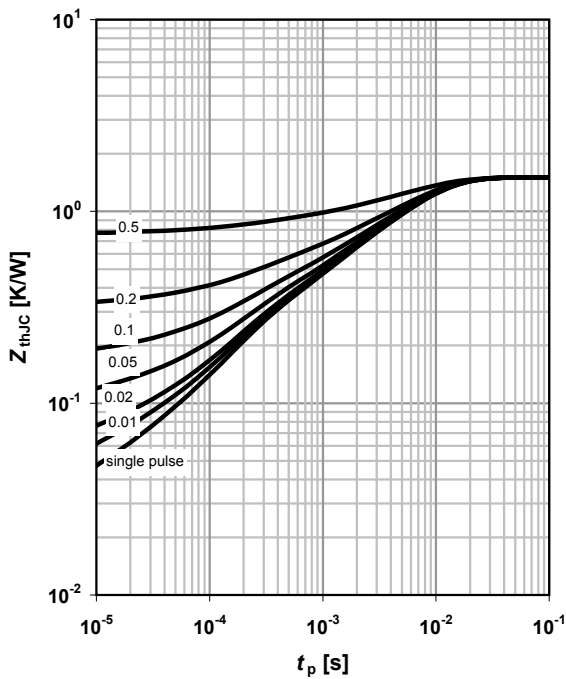
parameter: t_p



3 Max. transient thermal impedance

$I_D=f(V_{DS}); T_j=25\text{ °C}$

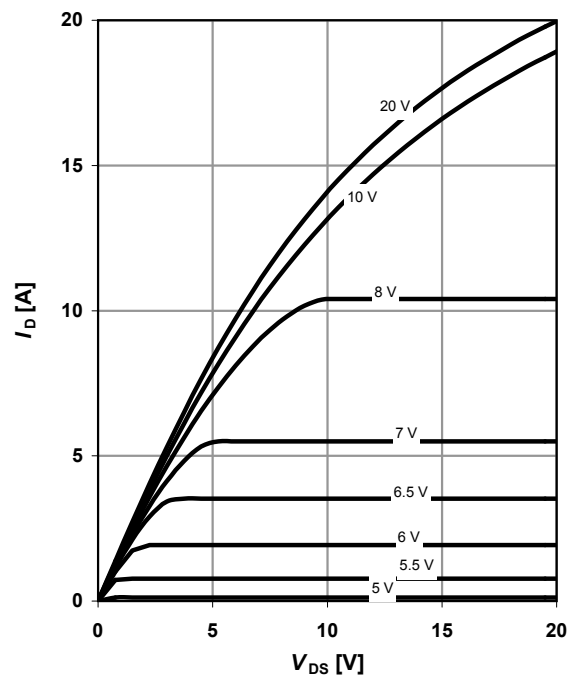
parameter: $D=t_p/T$



4 Typ. output characteristics

$I_D=f(V_{DS}); T_j=25\text{ °C}$

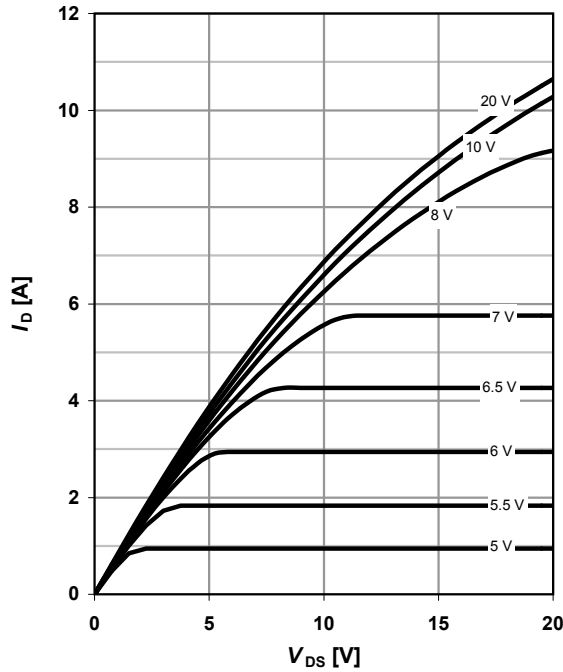
parameter: V_{GS}



5 Typ. output characteristics

$I_D = f(V_{DS}); T_j = 150\text{ }^\circ\text{C}$

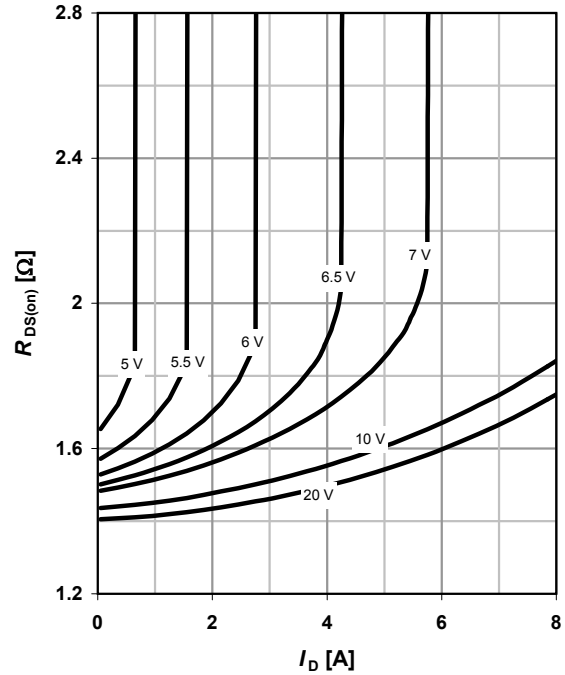
parameter: V_{GS}



6 Typ. drain-source on-state resistance

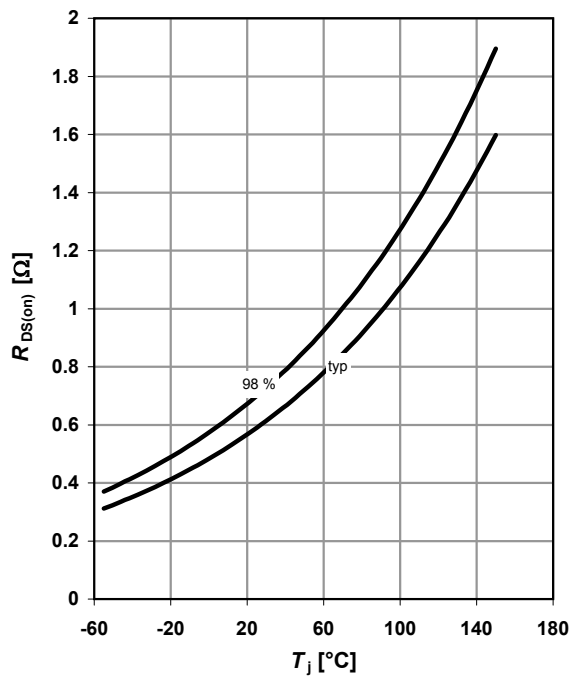
$R_{DS(on)} = f(I_D); T_j = 150\text{ }^\circ\text{C}$

parameter: V_{GS}



7 Drain-source on-state resistance

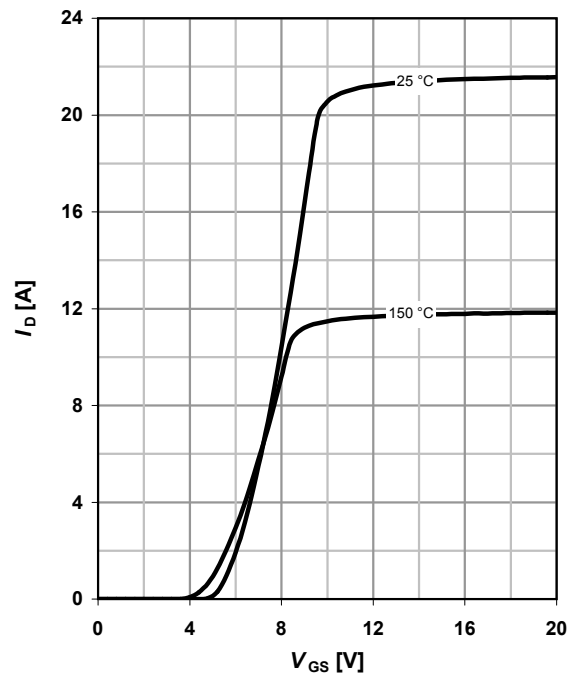
$R_{DS(on)} = f(T_j); I_D = 4.6\text{ A}; V_{GS} = 10\text{ V}$



8 Typ. transfer characteristics

$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

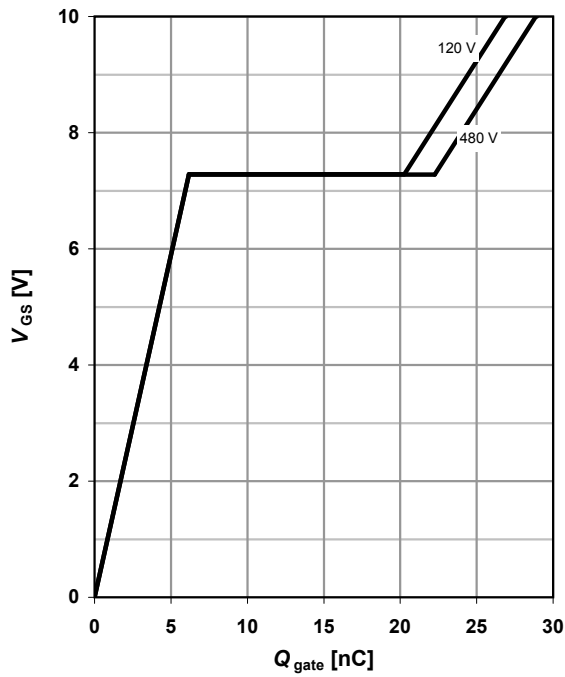
parameter: T_j



9 Typ. gate charge

$V_{GS}=f(Q_{gate}); I_D=6.6 \text{ A pulsed}$

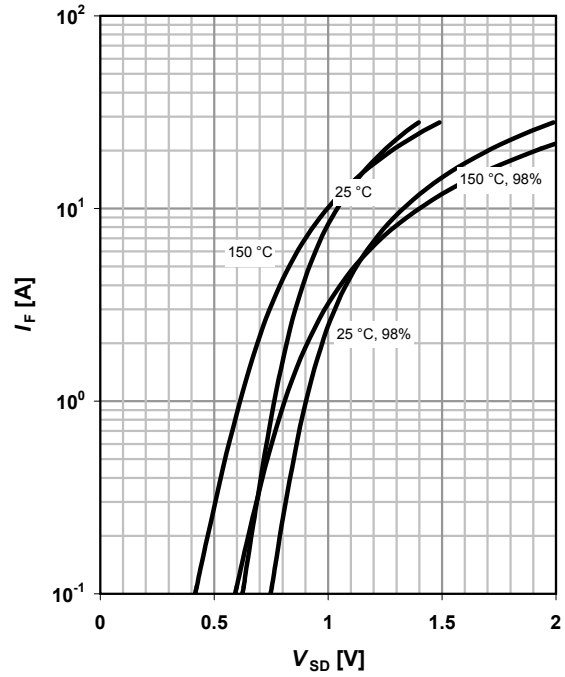
parameter: V_{DD}



10 Forward characteristics of reverse diode

$I_F=f(V_{SD})$

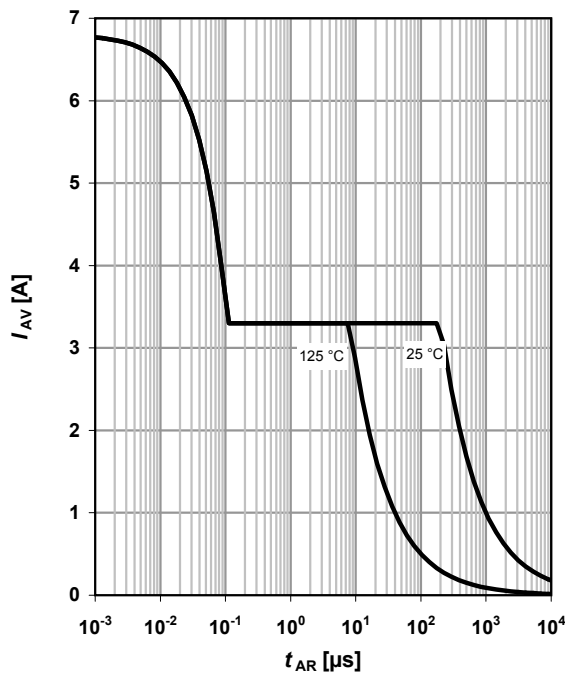
parameter: T_j



11 Avalanche SOA

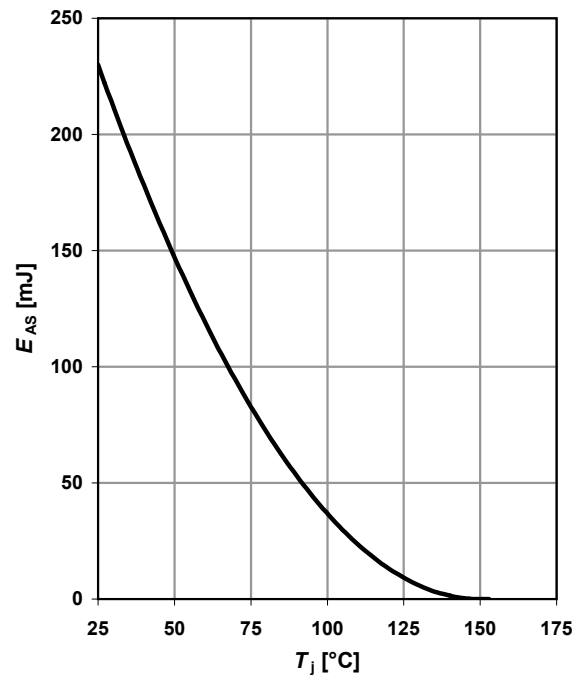
$I_{AR}=f(t_{AR})$

parameter: $T_{j(start)}$



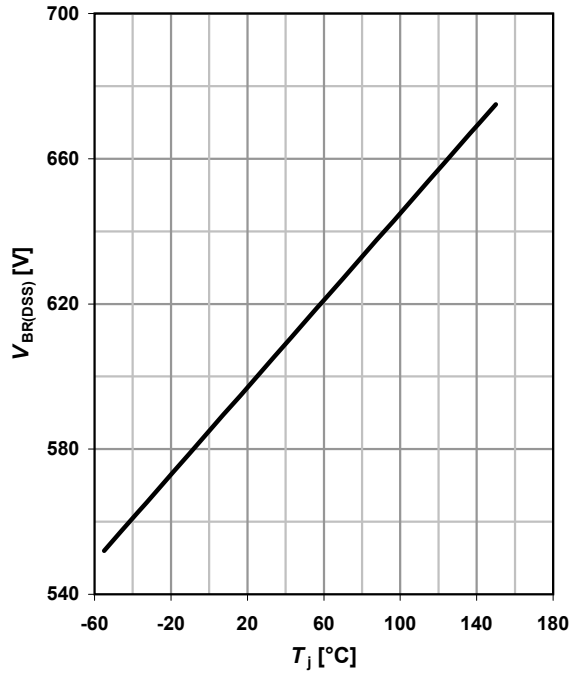
12 Avalanche energy

$E_{AS}=f(T_j); I_D=3.3 \text{ A}; V_{DD}=50 \text{ V}$



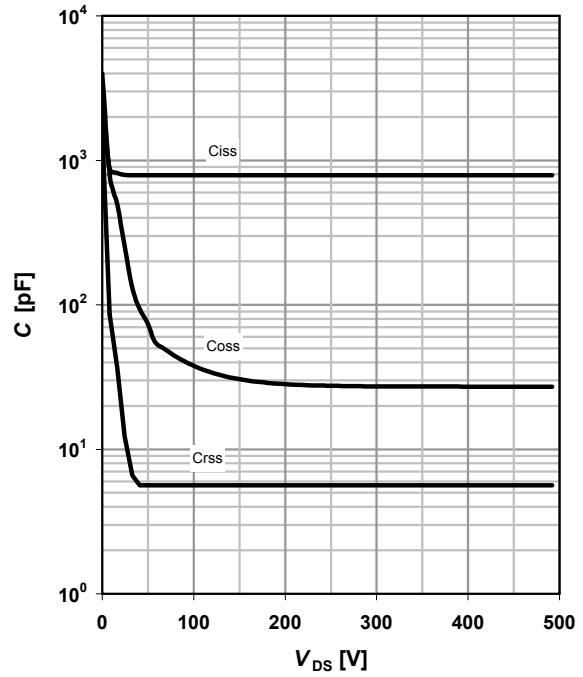
13 Drain-source breakdown voltage

$$V_{BR(DSS)} = f(T_j);$$



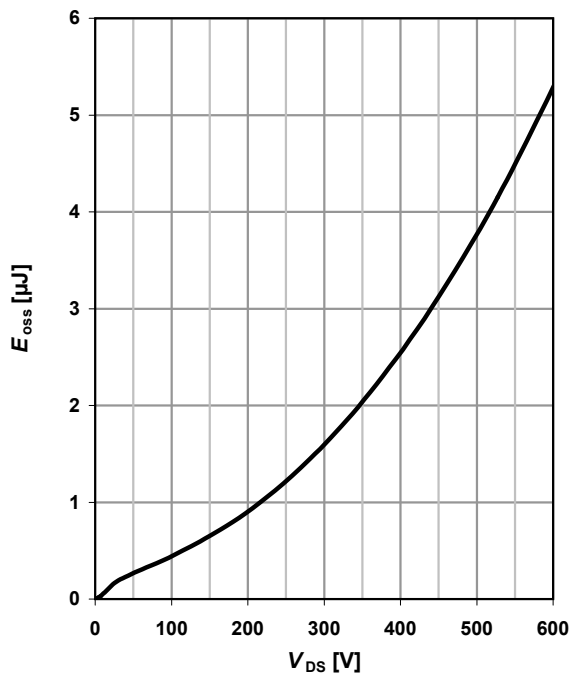
14 Typ. capacitances

$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$



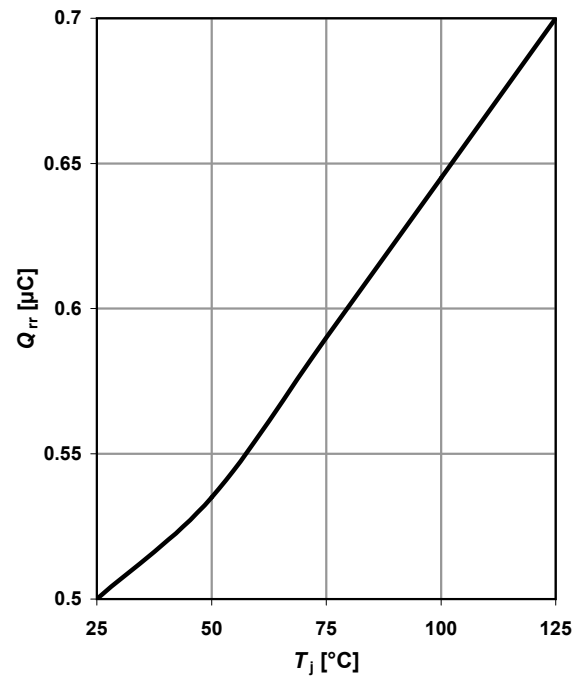
15 Typ. C_{oss} stored energy

$$E_{oss} = f(V_{DS})$$



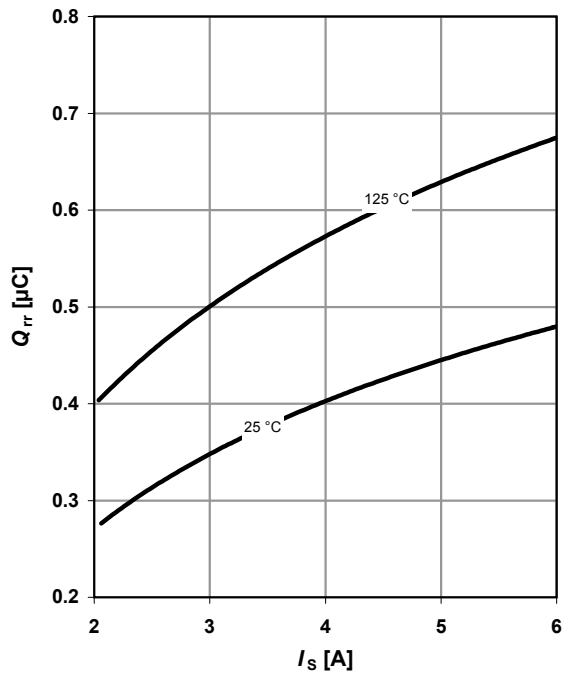
16 Typ. reverse recovery charge

$$Q_{rr} = f(T_j); \text{parameter: } I_D = 6.6 \text{ A}$$



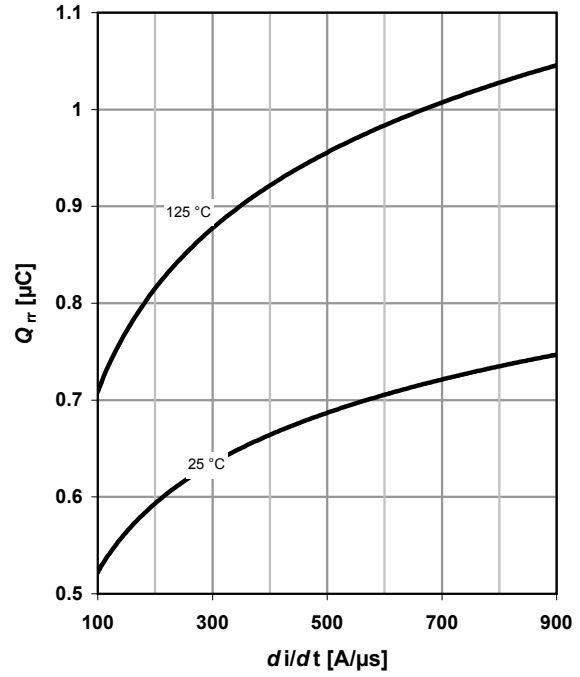
17 Typ. reverse recovery charge

$Q_{rr}=f(I_S)$; parameter: $di/dt=100\text{ A}/\mu\text{s}$

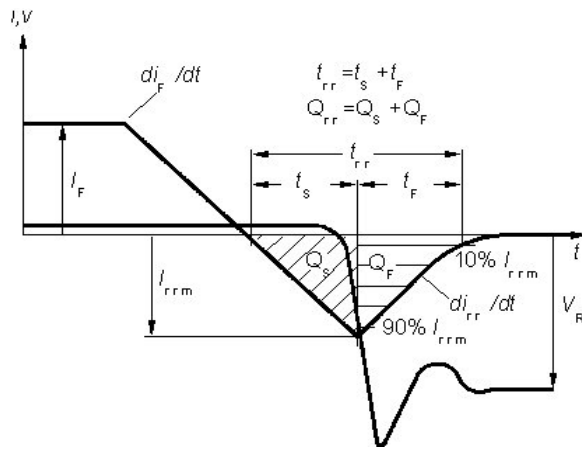


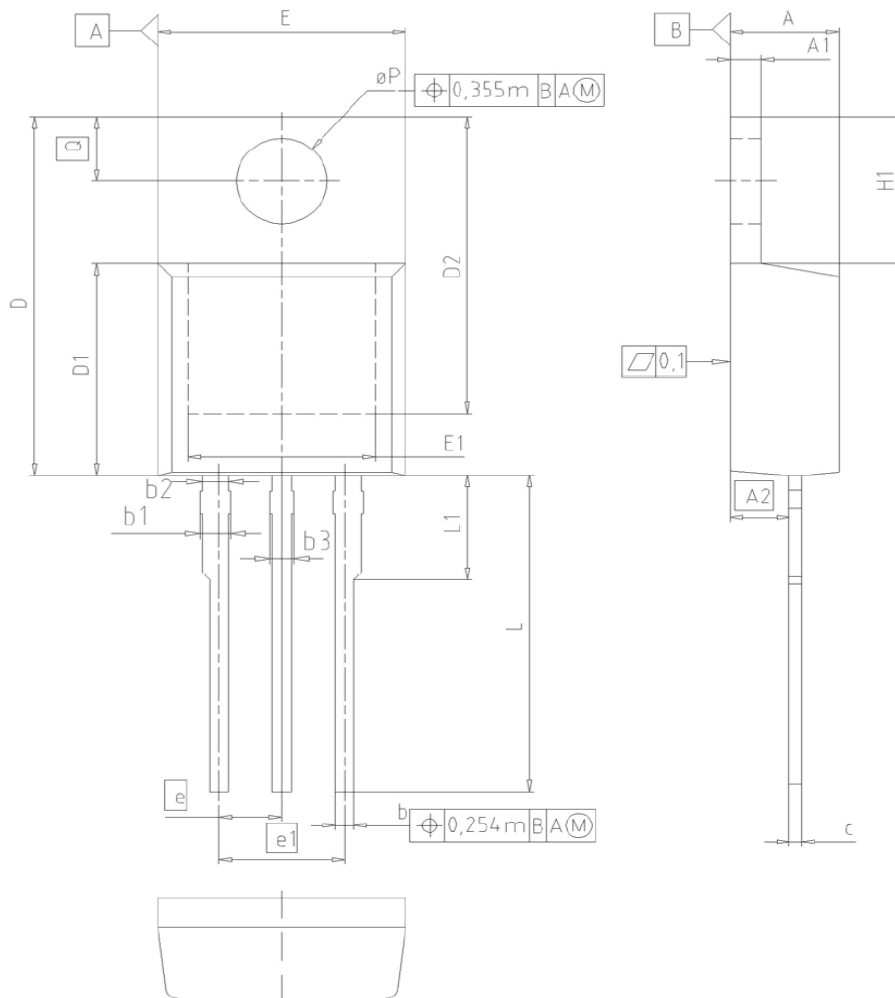
18 Typ. reverse recovery charge

$Q_{rr}=f(di/dt)$; parameter: $I_D=6.6\text{ A}$



Definition of diode switching characteristics





| DIM | MILLIMETERS | | INCHES | |
|-----|-------------|-------|--------|-------|
| | MIN | MAX | MIN | MAX |
| A | 4.30 | 4.57 | 0.169 | 0.180 |
| A1 | 1.17 | 1.40 | 0.046 | 0.055 |
| A2 | 2.15 | 2.72 | 0.085 | 0.107 |
| b | 0.65 | 0.86 | 0.026 | 0.034 |
| b1 | 0.95 | 1.40 | 0.037 | 0.055 |
| b2 | 0.95 | 1.15 | 0.037 | 0.045 |
| b3 | 0.65 | 1.15 | 0.026 | 0.045 |
| c | 0.33 | 0.60 | 0.013 | 0.024 |
| D | 14.81 | 15.95 | 0.583 | 0.628 |
| D1 | 8.51 | 9.45 | 0.335 | 0.372 |
| D2 | 12.19 | 13.10 | 0.480 | 0.516 |
| E | 9.70 | 10.36 | 0.382 | 0.408 |
| E1 | 6.50 | 8.60 | 0.256 | 0.339 |
| e | 2.54 | | 0.100 | |
| e1 | 5.08 | | 0.200 | |
| N | 3 | | 3 | |
| H1 | 5.90 | 6.90 | 0.232 | 0.272 |
| L | 13.00 | 14.00 | 0.512 | 0.551 |
| L1 | - | 4.80 | - | 0.189 |
| øP | 3.60 | 3.89 | 0.142 | 0.153 |
| Q | 2.60 | 3.00 | 0.102 | 0.118 |

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EUROPEAN PROJECTION

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05

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